



ABSTRACT OF THE DISCLOSURE

An optical detector with an arrangement of several semiconductor layers has at least one zone absorbing in a predetermined wavelength region, at least one zone which is at least partially light-permeable in the predetermined wavelength region, one semiconductor layer which is absorbing in the predetermined wavelength region, a semiconductor layer which is located under the first mentioned semiconductor layer and is at least partially light-permeable in the predetermined wavelength region, the at least one light-permeable zone is formed as an interruption in the absorbing semiconductor layer, and a throughgoing doping provided on an upper surface of the absorbing semiconductor layer which surrounds the interruption and at least a part of an upper surface of the at least partially light-permeable semiconductor layer, wherein the optical detector is produced by a new method and used for various applications.